## Announcements

- Welcome to the Wong Building!
- Ch. 4 solutions will be posted to WebCT on Friday.
- The deadline for WebCT quizzes is *extended*. You will have from the time it is posted until **7PM on Fridays**.
- Ch. 5 homework: 5.1, 5.2, 5.3, 5.8, 5.14, 5.23, 5.10, 5.11, 5.21, 5.28 plus one additional problem (see the problem set file on WebCT).

## Diffusion

• Self-diffusion: In an elemental solid, atoms also migrate.

Label some atoms



After some time





## Diffusion

• How do we quantify the amount or rate of diffusion?

 $J \equiv Flux \equiv \frac{moles (or mass) diffusing}{(surface area)(time)} = \frac{mol}{cm^2 s} or \frac{kg}{m^2 s}$ 

- Measured empirically
  - Make thin film (membrane) of known surface area
  - Impose concentration gradient
  - Measure how fast atoms or molecules diffuse through the membrane

$$J = \frac{M}{At} = \frac{I}{A} \frac{dM}{dt}$$

$$M = mass \\ diffused \\ time$$

Т



#### **Example: Chemical Protective Clothing (CPC)**

- Methylene chloride is a common ingredient of paint removers. Besides being an irritant, it also may be absorbed through skin. When using this paint remover, protective gloves should be worn.
- If butyl rubber gloves (0.04 cm thick) are used, what is the diffusive flux of methylene chloride through the glove?
- Data:
  - diffusion coefficient in butyl rubber:  $D = 110 \times 10^{-8} \text{ cm}^2/\text{s}$

– surface concentrations:

$$C_1 = 0.44 \text{ g/cm}^3$$
  
 $C_2 = 0.02 \text{ g/cm}^3$ 

## Example (cont).

• Solution – assuming linear conc. gradient



$$J = -(110 \times 10^{-8} \text{ cm}^2/\text{s}) \frac{(0.02 \text{ g/cm}^2 - 0.44 \text{ g/cm}^2)}{(0.04 \text{ cm})} = \frac{1.16 \times 10^{-5} \frac{\text{g}}{\text{cm}^2 \text{s}}}{1.16 \times 10^{-5} \frac{\text{g}}{\text{cm}^2 \text{s}}}$$

## **Diffusion Mechanisms**

• Interstitial diffusion – smaller atoms can diffuse between atoms.



Adapted from Fig. 5.3 (b), Callister 7e.

More rapid than vacancy diffusion

#### **Diffusion and Activation Barrier**





### **Diffusion and Temperature**

Diffusion coefficient increases with increasing T

$$D = D_o \exp\left(-\frac{Q_d}{RT}\right) \quad \mathbf{OR} \quad D = D_o \exp\left(\frac{Q_d}{k_bT}\right)$$

- D = diffusion coefficient [m<sup>2</sup>/s] or sometimes [cm<sup>2</sup>/s]
- $D_o$  = pre-exponential [m<sup>2</sup>/s] or sometimes [cm<sup>2</sup>/s]
- $Q_d$  = activation energy [J/mol or eV/atom]
- R = gas constant [8.314 J/mol-K]
- $k_b$  = Boltzmann's constant [8.617x10<sup>-5</sup> eV/atom-K]
- *T* = absolute temperature [K]

Diffusion coefficient, D (units? M2/s)  $D = \nu \lambda^2 = \nu_0 \lambda \exp\left(-\frac{\omega}{\kappa_b T}\right)$ What does D depend on o 1) A jump distance -> crystal structure (2) D. vibrational Frequency "Debye" (2) T Tincreases Dincrease (1) Q IF Q increases D decreasel (5) Diffusion mechanism

hysics  $\partial C$ Joing ford voltage  $\checkmark$ electromigration "special topic"



D varies with composition; e.g. C diff coeff in 0.15%C steel at 1000 °C  $=2.5 \times 10^{-11} \text{ m}^2 \text{s}^{-1}$ in 1.4%C  $=7.7 \times 10^{-11} \text{ m}^2 \text{s}^{-1}$ Because of lattice distortion

Net displacement US. prediction of D alone -p - CC diffusion  $@ 1000^{\circ}C$   $D = 2.5 \times 10^{-11} \text{ m}^2/\text{s}$ We said this resulted in 2× 10° jumps/s  $t = 1 \sec \qquad \lambda = 0.26 \, \text{nm}$ Total Appendistance is ~ 0.5 m RANDOM WALK

 $M(2) \rightarrow D \lambda^{L}$ n = Freq of jump x time

RANDOM WALK? Net displacement for njumps will be An Net disp = ANUt 1) = NDt

Net displacement US. prediction of D alone  

$$Fe - C$$
  
 $C$  diffusion @ 1000°C  $D = 2.5 \times 10^{-11} \text{ m}^2/\text{s}$   
 $(0.15\%C)$   
We said this resulted in  $2 \times 10^9 \text{ jumps/s}$   
 $t = 1 \sec$   $\Lambda = 0.26 \text{ nm}$   
To tal total distance is  $O.5 \text{ m}$  crazy  
However this a RANDOM WP L.K.  
Net disp. = N Dt  
 $\cong 5 \times 10^{-6} \text{ m} = 5 \text{ mm}$ 

TYPES OF DIFFUSION COEFFICIENTS (1) Self-diffusion coefficient Fe in Fe, Cu in Cu (2) Solute diffusion coefficient Civi Fe, Cuin Si CM in Chesny Si in Cuzsi 3 Interdiffusion coefficient D = Xcu Dsn + Xsn Dcn Icu Cussus/ n -> Cuesne

### **Diffusion and Temperature**

D has exponential dependence on T



Adapted from Fig. 5.7, *Callister 7e.* (Date for Fig. 5.7 taken from E.A. Brandes and G.B. Brook (Ed.) *Smithells Metals Reference Book*, 7th ed., Butterworth-Heinemann, Oxford, 1992.)



**Example:** At 500°C the diffusion coefficient and activation energy for Cu in Si are

 $D(500^{\circ}C) = 4 \times 10^{-13} \text{ m}^2/\text{s}$  $Q_d = 41.5 \text{ kJ/mol}$ 

What is the diffusion coefficient at 350°C?





# fort ? "Proprietany "Diffusion " Cu Interconnects Barrier



- Cu diffuses readily into Si
- Most chips require an elevated temperature processing step
- How do we manage to use Cu for integrated circuits?

## **Non-steady State Diffusion**

- The concentration of diffusing species is a function of both time and position C = C(x,t)
- In this case Fick's Second Law is used

Fick's Second Law



#### **Applications of Ficks 2nd law The Carburization of Steel**

increase in C concn to increase surface hardness/wear resistance



**Require time** to reach certain C concn to certain **depth** solve **Ficks 2nd law** using following boundary conditions

at x=0,  $C_B=C_s$  at  $x=\infty C_B=C_0$ 

$$\frac{C(x,t)-C_o}{C_s-C_o} = 1 - erf\left(\frac{x}{2\sqrt{Dt}}\right)$$

Solution D varies with C%

Take avg value



the specimen